

SavantIC Semiconductor

Product Specification

Silicon NPN Power Transistors

TIP31/31A/31B/31C

DESCRIPTION

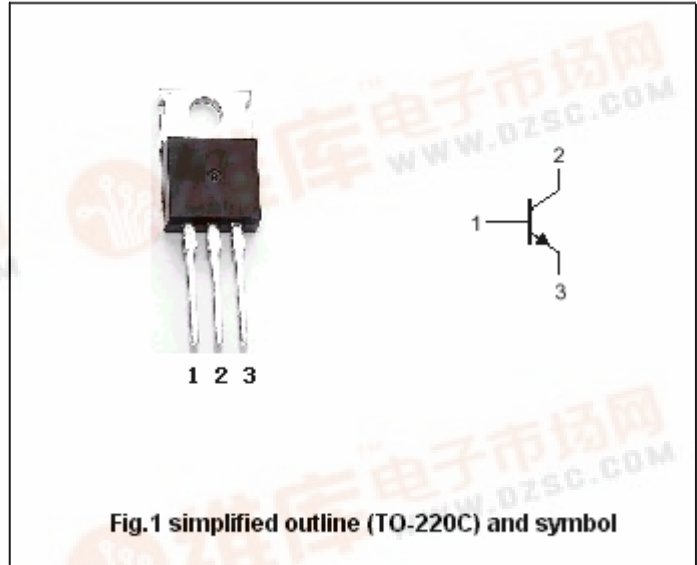
- With TO-220C package
- Complement to type TIP32/32A/32B/32C

APPLICATIONS

- Medium power linear switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



ABSOLUTE MAXIMUM RATINGS( $T_c=25^\circ C$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	TIP31	40	V
		TIP31A	60	
		TIP31B	80	
		TIP31C	100	
$V_{CEO}$	Collector-emitter voltage	TIP31	40	V
		TIP31A	60	
		TIP31B	80	
		TIP31C	100	
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current (DC)		3	A
$I_{CM}$	Collector current-Pulse		5	A
$I_B$	Base current		1	A
$P_C$	Collector power dissipation	$T_c=25^\circ C$	40	W
		$T_a=25^\circ C$	2	
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-65~150	$^\circ C$

## Silicon NPN Power Transistors

## TIP31/31A/31B/31C

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	TIP31	I <sub>C</sub> =30mA; I <sub>B</sub> =0	40			V
		TIP31A		60			
		TIP31B		80			
		TIP31C		100			
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =3A I <sub>B</sub> =0.375A			1.2	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =3A ; V <sub>CE</sub> =4V			1.8	V
I <sub>CES</sub>	Collector cut-off current	TIP31	V <sub>CE</sub> =40V; V <sub>EB</sub> =0			0.2	mA
		TIP31A	V <sub>CE</sub> =60V; V <sub>EB</sub> =0				
		TIP31B	V <sub>CE</sub> =80V; V <sub>EB</sub> =0				
		TIP31C	V <sub>CE</sub> =100V; V <sub>EB</sub> =0				
I <sub>CEO</sub>	Collector cut-off current	TIP31/31A	V <sub>CE</sub> =30V; I <sub>B</sub> =0			0.3	mA
		TIP31B/31C	V <sub>CE</sub> =60V; I <sub>B</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =1A ; V <sub>CE</sub> =4V	25			
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =3A ; V <sub>CE</sub> =4V	10		50	
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =0.5A ; V <sub>CE</sub> =10V	3			MHz

PACKAGE OUTLINE

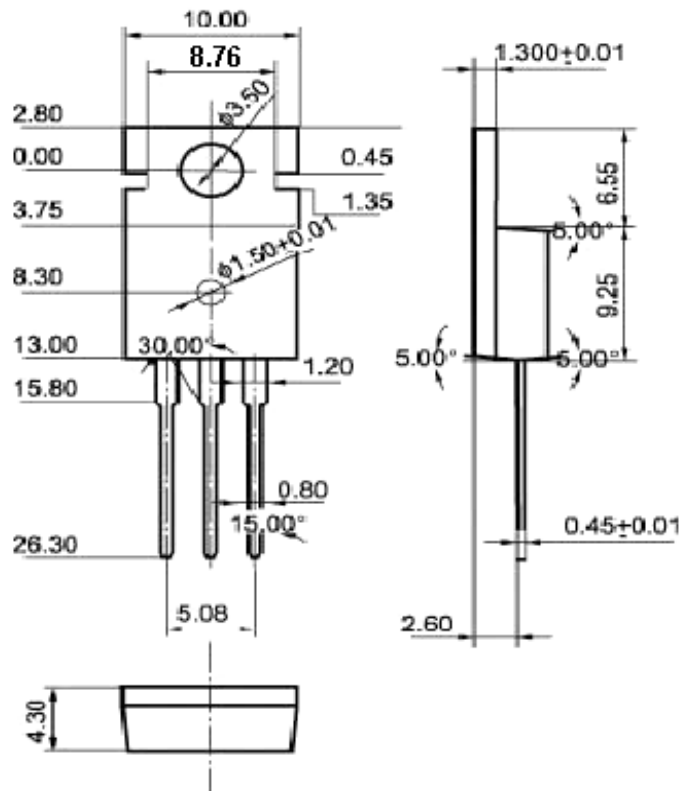


Fig.2 Outline dimensions (unindicated tolerance: ±0.10 mm)

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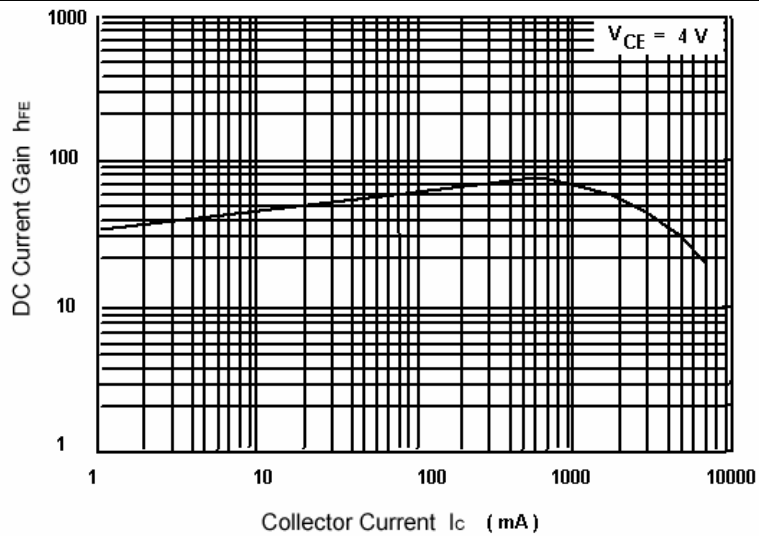


Fig.3 DC current Gain

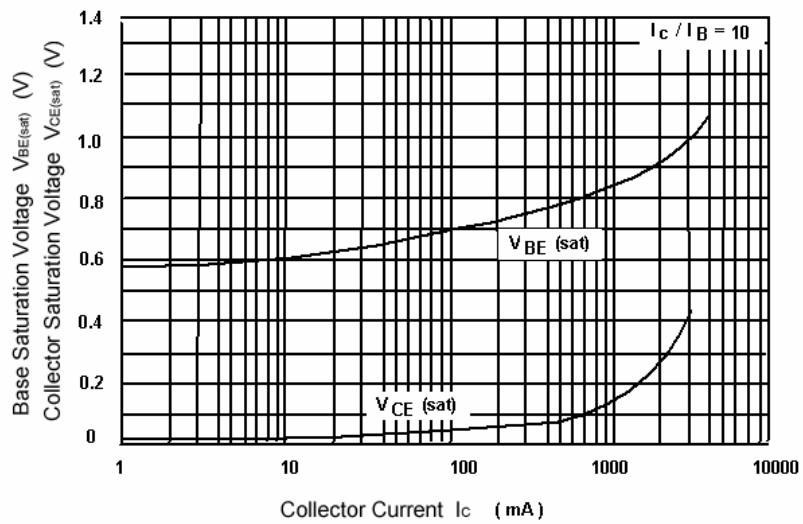


Fig.4 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

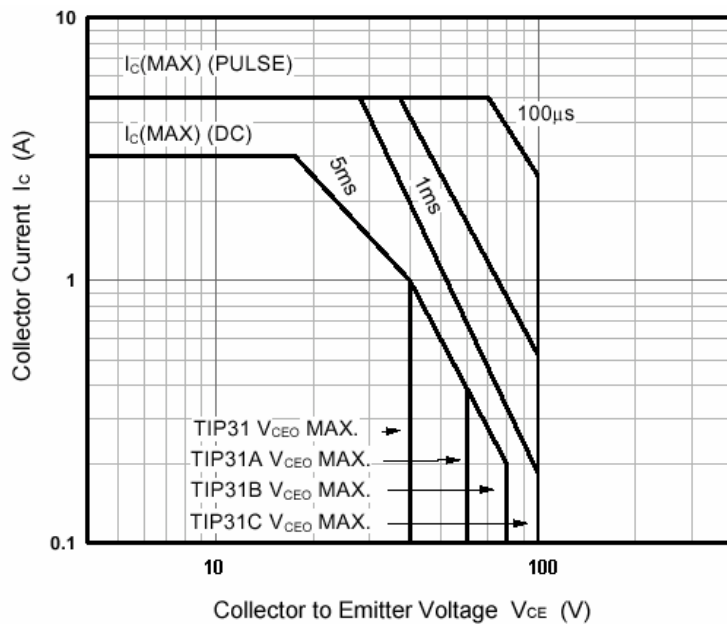


Fig.5 Safe Operating Area